

### INCHANGE SEMICONDUCTOR

# isc N-Channel MOSFET Transistor

# IXTP230N04T4

### • FEATURES

- With TO-220F packaging
- High speed switching
- · Low gate input resistance
- · Standard level gate drive
- · Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

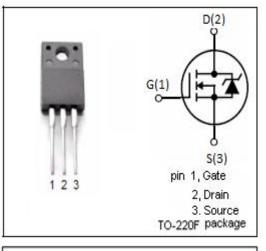
- Power supply
- Switching applications

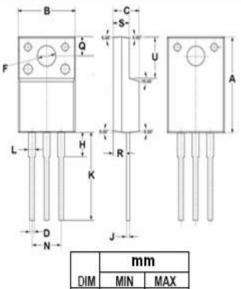
| • ABSOLUTE MAXIMUM RATINGS(Ta=25°C) |  |            |      |  |  |  |
|-------------------------------------|--|------------|------|--|--|--|
| SYMBOL                              | PARAMETER                                  | VALUE      | UNIT |  |  |  |
| V <sub>DSS</sub>                    | Drain-Source Voltage                       | 40         | V    |  |  |  |
| V <sub>GSS</sub>                    | Gate-Source Voltage                        | ±15        | ∧v   |  |  |  |
| ID                                  | Drain Current-Continuous@Tc=25℃<br>Tc=100℃ | 230<br>160 | Α    |  |  |  |
| I <sub>DM</sub>                     | Drain Current-Single Pulsed                | 700        | A    |  |  |  |
| PD                                  | Total Dissipation                          | 40         | W    |  |  |  |
| Tj                                  | Operating Junction Temperature             | 175        | °C   |  |  |  |
| T <sub>stg</sub>                    | Storage Temperature                        | -55~175    | °C   |  |  |  |

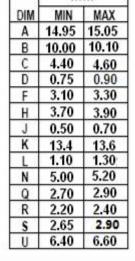
#### THERMAL CHARACTERISTICS

| SYMBOL    | PARAMETER                                 |  | UNIT |  |
|-----------|---|--|------|--|
| Rth(ch-c) | Channel-to-case thermal resistance 3.75   |  | °C/W |  |
| Rth(ch-a) | -a) Channel-to-ambient thermal resistance |  | °C/W |  |

1







### isc website: www.iscsemi.cn

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#### **ELECTRICAL CHARACTERISTICS**

 $T_{\text{C}}\text{=}25^\circ\!\!\mathbb{C}$  unless otherwise specified

| SYMBOL               | PARAMETER                      | CONDITIONS                                   | MIN | ТҮР | МАХ  | UNIT |
|----------------------|--------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>    | Drain-Source Breakdown Voltage | V <sub>GS</sub> =0V; I <sub>D</sub> = 0.25mA | 40  |     |      | V    |
| V <sub>GS</sub> (th) | Gate Threshold Voltage         | V <sub>DS</sub> =5V; I <sub>D</sub> =0.25mA  | 2.0 |     | 4.0  | V    |
| R <sub>DS(on)</sub>  | Drain-Source On-Resistance     | V <sub>GS</sub> = 10V; I <sub>D</sub> =110A  |     |     | 2.9  | mΩ   |
| I <sub>GSS</sub>     | Gate-Source Leakage Current    | V <sub>GS</sub> =±15V;V <sub>DS</sub> =0V    |     |     | ±0.2 | μA   |
| I <sub>DSS</sub>     | Drain-Source Leakage Current   | V <sub>DS</sub> = 40V; V <sub>GS</sub> = 0V; |     |     | 5    | μA   |
| V <sub>SDF</sub>     | Diode forward voltage          | I <sub>SD</sub> =100A, V <sub>GS</sub> = 0 V |     |     | 1.4  | V    |

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2